BFL4007

ON Semiconductor®

N-Channel Power MOSFET 600V, 14A, 0.68Ω, TO-220F-3FS

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Features

- Reverse recovery time t_{rr}=95ns (typ.)
- Input capacitance Ciss=1200pF (typ.)
- ON-resistance RDS(on)= 0.52Ω (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

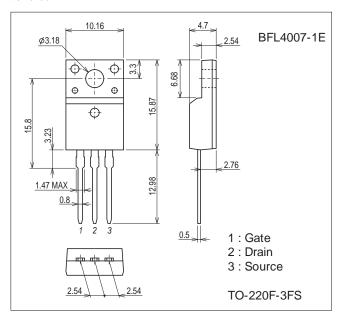
Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		600	V
Gate to Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	14	Α
	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	8.7	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	49	Α
Source to Drain Diode Forward Current (DC)	Is		14	Α
Source to Drain Diode Forward Current (Pulse)	ISP	PW≤10μs, duty cycle≤1%	49	Α
Allowable Power Dissipation	PD		2.0	W
		Tc=25°C (Our ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		196	mJ
Avalanche Current *5	I _{AV}		8.5	Α

Note: *1 Shows chip capability

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

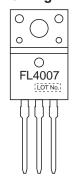
unit : mm (typ) 7528-001



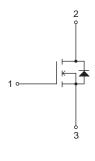
Ordering & Package Information

Device	Package	Shipping	memo	
BFL4007-1E	TO-220F-3FS SC-67	50 pcs./tube	Pb-Free	

Marking



Electrical Connection



^{*2} Package limited

^{*3} Our condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

^{*4} VDD=50V, L=5mH, IAV=8.5A (Fig.1)

^{*5} L≤5mH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =7A	4.3	8.5		S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D =7A, V _G S=10V		0.52	0.68	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		1200		pF
Output Capacitance	Coss			220		pF
Reverse Transfer Capacitance	Crss			43		pF
Turn-ON Delay Time	t _d (on)	See Fig.2		27		ns
Rise Time	tr			72		ns
Turn-OFF Delay Time	t _d (off)			122		ns
Fall Time	tf			48		ns
Total Gate Charge	Qg			46		nC
Gate to Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =14A		8.6		nC
Gate to Drain "Miller" Charge	Qgd			26.4		nC
Diode Forward Voltage	V _{SD}	I _S =14A, V _{GS} =0V		1.1	1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		95		ns
Reverse Recovery Charge	Q _{rr}	IS=14A, VGS=0V, di/dt=100A/μs		250		nC

Fig.1 Unclamped Inductive Switching Test Circuit

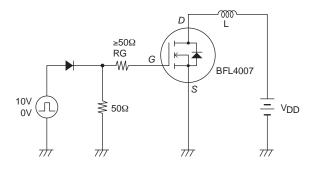


Fig.2 Switching Time Test Circuit

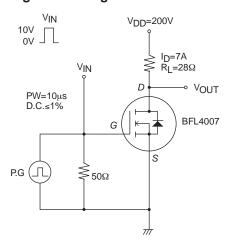
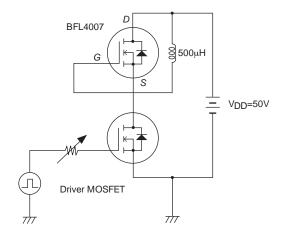
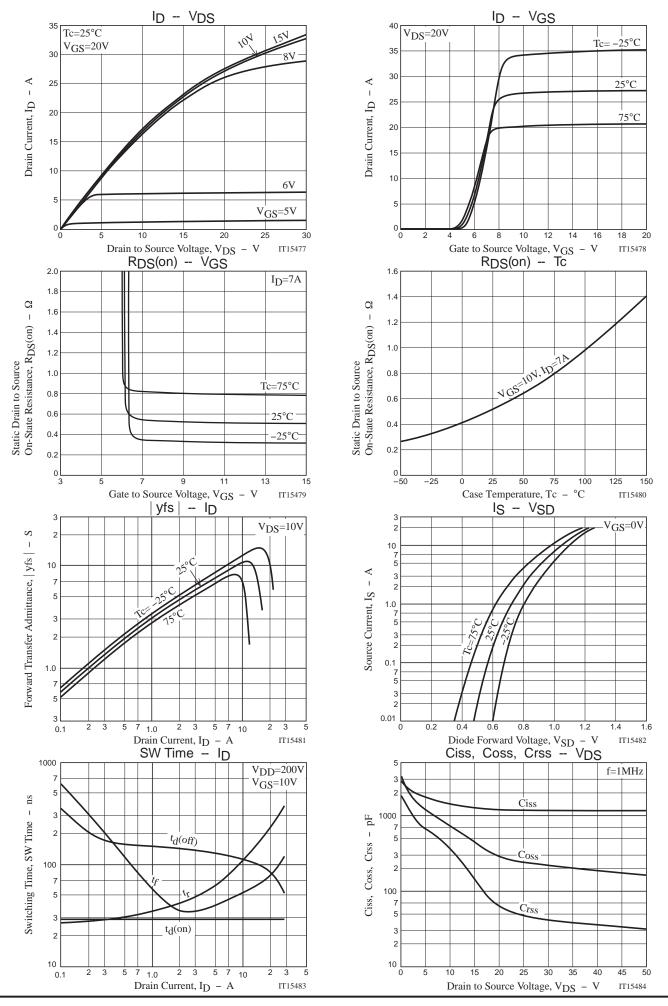
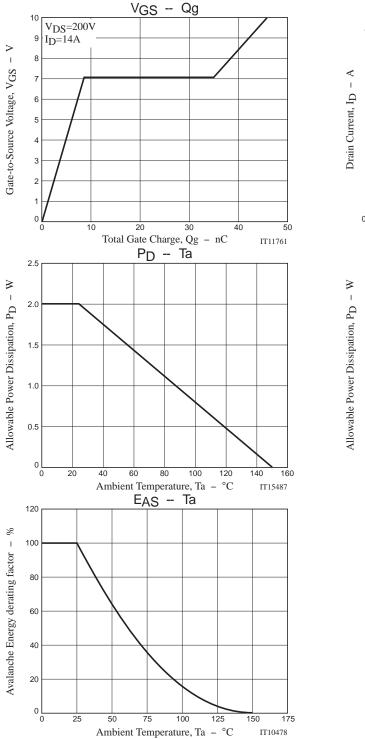
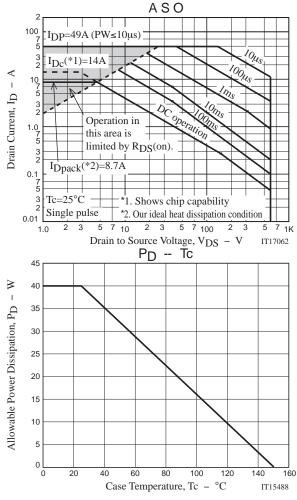


Fig.3 Reverse Recovery Time Test Circuit



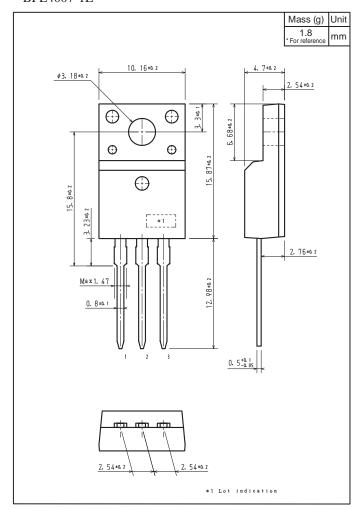






Outline Drawing

BFL4007-1E



Note on usage: Since the BFL4007 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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